# E·XFL



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#### Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

#### **Applications of Embedded - FPGAs**

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

#### Details

Product Status	Active
Number of LABs/CLBs	·
Number of Logic Elements/Cells	- ·
Total RAM Bits	36864
Number of I/O	68
Number of Gates	250000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	100-TQFP
Supplier Device Package	100-VQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/m1a3p250-1vq100i

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong



0-I/O is set to drive out logic Low

Last Known State – I/O is set to the last value that was driven out prior to entering the programming mode, and then held at that value during programming

Z -Tristate: I/O is tristated

om file Save to file			Show BSR De
Port Name	Macro Cell	Pin Number	1/O State (Output Only)
BIST	ADLIB:INBUF	T2	1
BYPASS_IO	ADLIB:INBUF	K1	1
CLK	ADLIB:INBUF	B1	1
ENOUT	ADLIB:INBUF	J16	1
LED	ADLIB:OUTBUF	M3	0
MONITOR[0]	ADLIB:OUTBUF	B5	0
MONITOR[1]	ADLIB:OUTBUF	C7	Z
MONITOR[2]	ADLIB:OUTBUF	D9	Z
MONITOR[3]	ADLIB:OUTBUF	D7	Z
MONITOR[4]	ADLIB:OUTBUF	A11	Z
OEa	ADLIB:INBUF	E4	Z
ОЕЬ	ADLIB:INBUF	F1	Z
OSC_EN	ADLIB:INBUF	К3	Z
PAD(10)	ADLIB:BIBUF_LVCMOS33U	M8	Z
PAD[11]	ADLIB:BIBUF_LVCMOS33D	R7	Z
PAD[12]	ADLIB:BIBUF_LVCMOS33U	D11	Z
PAD[13]	ADLIB:BIBUF_LVCMOS33D	C12	Z
PAD[14]	ADLIB:BIBUF_LVCMOS33U	R6	Z

### Figure 1-4 • I/O States During Programming Window

- 6. Click OK to return to the FlashPoint Programming File Generator window.
- Note: I/O States During programming are saved to the ADB and resulting programming files after completing programming file generation.



# I/O Power-Up and Supply Voltage Thresholds for Power-On Reset (Commercial and Industrial)

Sophisticated power-up management circuitry is designed into every ProASIC<sup>®</sup>3 device. These circuits ensure easy transition from the powered-off state to the powered-up state of the device. The many different supplies can power up in any sequence with minimized current spikes or surges.

In addition, the I/O will be in a known state through the power-up sequence. The basic principle is shown in Figure 2-2 on page 2-5.

There are five regions to consider during power-up.

ProASIC3 I/Os are activated only if ALL of the following three conditions are met:

- 1. VCC and VCCI are above the minimum specified trip points (Figure 2-2 on page 2-5).
- 2. VCCI > VCC 0.75 V (typical)
- 3. Chip is in the operating mode.

#### VCCI Trip Point:

```
Ramping up: 0.6 V < trip_point_up < 1.2 V
Ramping down: 0.5 V < trip_point_down < 1.1 V
```

#### VCC Trip Point:

```
Ramping up: 0.6 V < trip_point_up < 1.1 V
Ramping down: 0.5 V < trip_point_down < 1 V
```

VCC and VCCI ramp-up trip points are about 100 mV higher than ramp-down trip points. This specifically built-in hysteresis prevents undesirable power-up oscillations and current surges. Note the following:

- During programming, I/Os become tristated and weakly pulled up to VCCI.
- JTAG supply, PLL power supplies, and charge pump VPUMP supply have no influence on I/O behavior.

# PLL Behavior at Brownout Condition

Microsemi recommends using monotonic power supplies or voltage regulators to ensure proper power-up behavior. Power ramp-up should be monotonic at least until VCC and VCCPLLX exceed brownout activation levels. The VCC activation level is specified as 1.1 V worst-case (see Figure 2-2 on page 2-5 for more details).

When PLL power supply voltage and/or VCC levels drop below the VCC brownout levels (0.75 V  $\pm$  0.25 V), the PLL output lock signal goes low and/or the output clock is lost. Refer to the "Power-Up/Down Behavior of Low Power Flash Devices" chapter of the *ProASIC3 FPGA Fabric User's Guide* for information on clock and lock recovery.

### Internal Power-Up Activation Sequence

- 1. Core
- 2. Input buffers

Output buffers, after 200 ns delay from input buffer activation.

# **Thermal Characteristics**

### Introduction

The temperature variable in the Microsemi Designer software refers to the junction temperature, not the ambient temperature. This is an important distinction because dynamic and static power consumption cause the chip junction to be higher than the ambient temperature.

EQ can be used to calculate junction temperature.

 $T_J$  = Junction Temperature =  $\Delta T + T_A$ 

where:

T<sub>A</sub> = Ambient Temperature

 $\Delta T$  = Temperature gradient between junction (silicon) and ambient  $\Delta T$  =  $\theta_{ia}$  \* P

 $\theta_{ia}$  = Junction-to-ambient of the package.  $\theta_{ia}$  numbers are located in Table 2-5 on page 2-6.

P = Power dissipation



### RAM Contribution—P<sub>MEMORY</sub>

 $\mathsf{P}_{\mathsf{MEMORY}} = \mathsf{P}_{\mathsf{AC11}} * \mathsf{N}_{\mathsf{BLOCKS}} * \mathsf{F}_{\mathsf{READ-CLOCK}} * \beta_2 + \mathsf{P}_{\mathsf{AC12}} * \mathsf{N}_{\mathsf{BLOCK}} * \mathsf{F}_{\mathsf{WRITE-CLOCK}} * \beta_3$ 

 $N_{\mbox{\scriptsize BLOCKS}}$  is the number of RAM blocks used in the design.

F<sub>READ-CLOCK</sub> is the memory read clock frequency.

 $\beta_2$  is the RAM enable rate for read operations.

F<sub>WRITE-CLOCK</sub> is the memory write clock frequency.

 $\beta_3$  is the RAM enable rate for write operations—guidelines are provided in Table 2-17 on page 2-14.

## PLL Contribution—P<sub>PLL</sub>

 $P_{PLL} = P_{DC4} + P_{AC13} * F_{CLKOUT}$ 

F<sub>CLKOUT</sub> is the output clock frequency.<sup>1</sup>

## Guidelines

#### Toggle Rate Definition

A toggle rate defines the frequency of a net or logic element relative to a clock. It is a percentage. If the toggle rate of a net is 100%, this means that this net switches at half the clock frequency. Below are some examples:

- The average toggle rate of a shift register is 100% because all flip-flop outputs toggle at half of the clock frequency.
- The average toggle rate of an 8-bit counter is 25%:
  - Bit 0 (LSB) = 100%
  - Bit 1 = 50%
  - Bit 2 = 25%
  - ...
  - Bit 7 (MSB) = 0.78125%
  - Average toggle rate = (100% + 50% + 25% + 12.5% + . . . + 0.78125%) / 8

#### Enable Rate Definition

Output enable rate is the average percentage of time during which tristate outputs are enabled. When nontristate output buffers are used, the enable rate should be 100%.

#### Table 2-16 • Toggle Rate Guidelines Recommended for Power Calculation

Component	Definition	Guideline
$\alpha_1$	Toggle rate of VersaTile outputs	10%
α <sub>2</sub>	I/O buffer toggle rate	10%

#### Table 2-17 • Enable Rate Guidelines Recommended for Power Calculation

Component	Definition	Guideline
β <sub>1</sub>	I/O output buffer enable rate	100%
β <sub>2</sub>	RAM enable rate for read operations	12.5%
β <sub>3</sub>	RAM enable rate for write operations	12.5%

The PLL dynamic contribution depends on the input clock frequency, the number of output clock signals generated by the PLL, and the frequency of each output clock. If a PLL is used to generate more than one output clock, include each output clock in the formula by adding its corresponding contribution (P<sub>AC14</sub> \* F<sub>CLKOUT</sub> product) to the total PLL contribution.



# Single-Ended I/O Characteristics

# 3.3 V LVTTL / 3.3 V LVCMOS

Low-Voltage Transistor–Transistor Logic (LVTTL) is a general-purpose standard (EIA/JESD) for 3.3 V applications. It uses an LVTTL input buffer and push-pull output buffer.

#### Table 2-37 • Minimum and Maximum DC Input and Output Levels Applicable to Advanced I/O Banks

3.3 V LVTTL / 3.3 V LVCMOS	v	IL	v	н	VOL	VОН	IOL	юн	IOSL	IOSH	IIL¹	IIH <sup>2</sup>
Drive Strength	Min V	Max V	Min V	Max V	Max V	Min V	mA	mA	Max mA <sup>3</sup>	Max mA <sup>3</sup>	μA <sup>4</sup>	μA <sup>4</sup>
2 mA	-0.3	0.8	2	3.6	0.4	2.4	2	2	27	25	10	10
4 mA	-0.3	0.8	2	3.6	0.4	2.4	4	4	27	25	10	10
6 mA	-0.3	0.8	2	3.6	0.4	2.4	6	6	54	51	10	10
8 mA	-0.3	0.8	2	3.6	0.4	2.4	8	8	54	51	10	10
12 mA	-0.3	0.8	2	3.6	0.4	2.4	12	12	109	103	10	10
16 mA	-0.3	0.8	2	3.6	0.4	2.4	16	16	127	132	10	10
24 mA	-0.3	0.8	2	3.6	0.4	2.4	24	24	181	268	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where -0.3 V < VIN < VIL.

2. IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges

- 3. Currents are measured at 100°C junction temperature and maximum voltage.
- 4. Currents are measured at 85°C junction temperature.
- 5. Software default selection highlighted in gray.

# Table 2-38 • Minimum and Maximum DC Input and Output Levels Applicable to Standard Plus I/O Banks

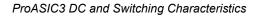
3.3 V LVTTL / 3.3 V LVCMOS	V	ΊL	V	ΊH	VOL	VOH	IOL	ЮН	IOSL	IOSH	IIL <sup>1</sup>	IIH <sup>2</sup>
Drive Strength	Min V	Max V	Min V	Max V	Max V	Min V	mA	mA	Max mA <sup>3</sup>	Max mA <sup>3</sup>	μA <sup>4</sup>	μA <sup>4</sup>
2 mA	-0.3	0.8	2	3.6	0.4	2.4	2	2	27	25	10	10
4 mA	-0.3	0.8	2	3.6	0.4	2.4	4	4	27	25	10	10
6 mA	-0.3	0.8	2	3.6	0.4	2.4	6	6	54	51	10	10
8 mA	-0.3	0.8	2	3.6	0.4	2.4	8	8	54	51	10	10
12 mA	-0.3	0.8	2	3.6	0.4	2.4	12	12	109	103	10	10
16 mA	-0.3	0.8	2	3.6	0.4	2.4	16	16	109	103	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.

2. IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges

- 3. Currents are measured at 100°C junction temperature and maximum voltage.
- 4. Currents are measured at 85°C junction temperature.
- 5. Software default selection highlighted in gray.





# Table 2-54 • 3.3 V LVTTL / 3.3 V LVCMOS High Slew Commercial-Case Conditions: TJ = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V

	Applicable to	Stanuaru i		S								
Drive Strength	Equiv. Software Default Drive Strength Option <sup>1</sup>	Speed Grade	t <sub>dout</sub>	t <sub>DP</sub>	t <sub>DIN</sub>	t <sub>PY</sub>	t <sub>eout</sub>	t <sub>ZL</sub>	t <sub>ZH</sub>	t <sub>LZ</sub>	t <sub>HZ</sub>	Units
100 µA	2 mA	Std.	0.60	10.93	0.04	1.52	0.43	10.93	9.46	3.20	3.32	ns
		-1	0.51	9.29	0.04	1.29	0.36	9.29	8.04	2.72	2.82	ns
		-2	0.45	8.16	0.03	1.13	0.32	8.16	7.06	2.39	2.48	ns
100 µA	4 mA	Std.	0.60	10.93	0.04	1.52	0.43	10.93	9.46	3.20	3.32	ns
		-1	0.51	9.29	0.04	1.29	0.36	9.29	8.04	2.72	2.82	ns
		-2	0.45	8.16	0.03	1.13	0.32	8.16	7.06	2.39	2.48	ns
100 µA	6 mA	Std.	0.60	6.82	0.04	1.52	0.43	6.82	5.70	3.70	4.16	ns
		-1	0.51	5.80	0.04	1.29	0.36	5.80	4.85	3.15	3.54	ns
		-2	0.45	5.09	0.03	1.13	0.32	5.09	4.25	2.77	3.11	ns
100 µA	8 mA	Std.	0.60	6.82	0.04	1.52	0.43	6.82	5.70	3.70	4.16	ns
		-1	0.51	5.80	0.04	1.29	0.36	5.80	4.85	3.15	3.54	ns
		-2	0.45	5.09	0.03	1.13	0.32	5.09	4.25	2.77	3.11	ns

Notes:

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is  $\pm 100 \ \mu$ A. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.

2. Software default selection highlighted in gray.

3. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.



# 3.3 V PCI, 3.3 V PCI-X

Peripheral Component Interface for 3.3 V standard specifies support for 33 MHz and 66 MHz PCI Bus applications.

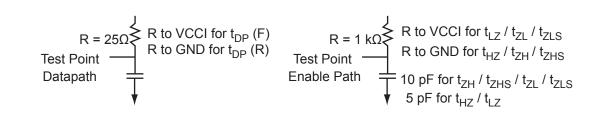
3.3 V PCI/PCI-X	V	ΊL	V	IH	VOL	VOH	IOL	ЮН	IOSL	IOSH	IIL	IIH
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max,. V	Min. V	mA	mA	Max. mA <sup>1</sup>	Max. mA <sup>1</sup>	μA²	μA²
Per PCI specification					Per PCI	curves					10	10

Notes:

1. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.

2. Currents are measured at 85°C junction temperature.

AC loadings are defined per the PCI/PCI-X specifications for the datapath; Microsemi loadings for enable path characterization are described in Figure 2-11.



### Figure 2-11 • AC Loading

AC loadings are defined per PCI/PCI-X specifications for the datapath; Microsemi loading for tristate is described in Table 2-87.

#### Table 2-87 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	C <sub>LOAD</sub> (pF)
0	3.3	0.285 * VCCI for t <sub>DP(R)</sub>	10
		0.615 * VCCI for t <sub>DP(F)</sub>	

Note: \*Measuring point = V<sub>trip.</sub> See Table 2-22 on page 2-22 for a complete table of trip points.



Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t <sub>oclkq</sub>	Clock-to-Q of the Output Data Register	HH, DOUT
tosud	Data Setup Time for the Output Data Register	FF, HH
t <sub>OHD</sub>	Data Hold Time for the Output Data Register	FF, HH
tosue	Enable Setup Time for the Output Data Register	GG, HH
t <sub>OHE</sub>	Enable Hold Time for the Output Data Register	GG, HH
t <sub>OCLR2Q</sub>	Asynchronous Clear-to-Q of the Output Data Register	LL, DOUT
t <sub>OREMCLR</sub>	Asynchronous Clear Removal Time for the Output Data Register	LL, HH
t <sub>ORECCLR</sub>	Asynchronous Clear Recovery Time for the Output Data Register	LL, HH
t <sub>oeclkq</sub>	Clock-to-Q of the Output Enable Register	HH, EOUT
toesud	Data Setup Time for the Output Enable Register	JJ, HH
t <sub>OEHD</sub>	Data Hold Time for the Output Enable Register	JJ, HH
tOESUE	Enable Setup Time for the Output Enable Register	KK, HH
t <sub>OEHE</sub>	Enable Hold Time for the Output Enable Register	KK, HH
t <sub>OECLR2Q</sub>	Asynchronous Clear-to-Q of the Output Enable Register	II, EOUT
t <sub>OEREMCLR</sub>	Asynchronous Clear Removal Time for the Output Enable Register	II, HH
t <sub>OERECCLR</sub>	Asynchronous Clear Recovery Time for the Output Enable Register	II, HH
t <sub>ICLKQ</sub>	Clock-to-Q of the Input Data Register	AA, EE
t <sub>ISUD</sub>	Data Setup Time for the Input Data Register	CC, AA
t <sub>IHD</sub>	Data Hold Time for the Input Data Register	CC, AA
t <sub>ISUE</sub>	Enable Setup Time for the Input Data Register	BB, AA
t <sub>IHE</sub>	Enable Hold Time for the Input Data Register	BB, AA
t <sub>ICLR2Q</sub>	Asynchronous Clear-to-Q of the Input Data Register	DD, EE
t <sub>IREMCLR</sub>	Asynchronous Clear Removal Time for the Input Data Register	DD, AA
t <sub>IRECCLR</sub>	Asynchronous Clear Recovery Time for the Input Data Register	DD, AA

#### Table 2-97 • Parameter Definition and Measuring Nodes

Note: \*See Figure 2-16 on page 2-71 for more information.



# Output Enable Register

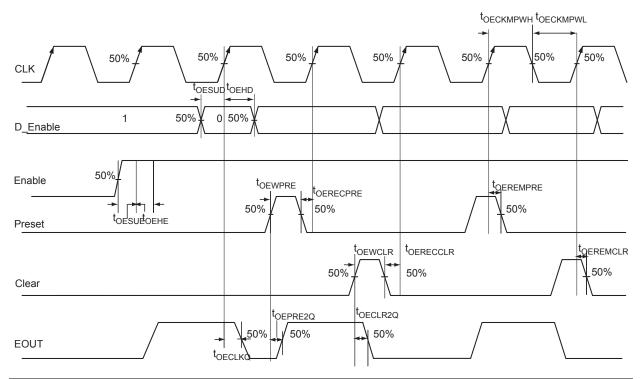


Figure 2-19 • Output Enable Register Timing Diagram



Parameter	Description	-2	-1	Std.	Units
t <sub>AS</sub>	Address setup time	0.25	0.28	0.33	ns
t <sub>AH</sub>	Address hold time	0.00	0.00	0.00	ns
t <sub>ENS</sub>	REN, WEN setup time	0.13	0.15	0.17	ns
t <sub>ENH</sub>	REN, WEN hold time	0.10	0.11	0.13	ns
t <sub>DS</sub>	Input data (WD) setup time	0.18	0.21	0.25	ns
t <sub>DH</sub>	Input data (WD) hold time	0.00	0.00	0.00	ns
t <sub>CKQ1</sub>	Clock High to new data valid on RD (output retained)	2.16	2.46	2.89	ns
t <sub>CKQ2</sub>	Clock High to new data valid on RD (pipelined)	0.90	1.02	1.20	ns
t <sub>C2CRWH</sub> 1	Address collision clk-to-clk delay for reliable read access after write on same address—Applicable to Opening Edge	0.50	0.43	0.38	ns
t <sub>C2CWRH</sub> 1	Address collision clk-to-clk delay for reliable write access after read on same address—Applicable to Opening Edge	0.59	0.50	0.44	ns
t <sub>RSTBQ</sub>	RESET Low to data out Low on RD (flow-through)	0.92	1.05	1.23	ns
	RESET Low to data out Low on RD (pipelined)	0.92	1.05	1.23	ns
t <sub>REMRSTB</sub>	RESET removal	0.29	0.33	0.38	ns
t <sub>RECRSTB</sub>	RESET recovery	1.50	1.71	2.01	ns
t <sub>MPWRSTB</sub>	RESET minimum pulse width	0.21	0.24	0.29	ns
t <sub>CYC</sub>	Clock cycle time	3.23	3.68	4.32	ns
F <sub>MAX</sub>	Maximum frequency	310	272	231	MHz

#### Table 2-117 • RAM512X18

Commercial-Case Conditions: T<sub>J</sub> = 70°C, Worst-Case VCC = 1.425 V

Notes:

1. For more information, refer to the application note Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs.

2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.



# **FIFO**

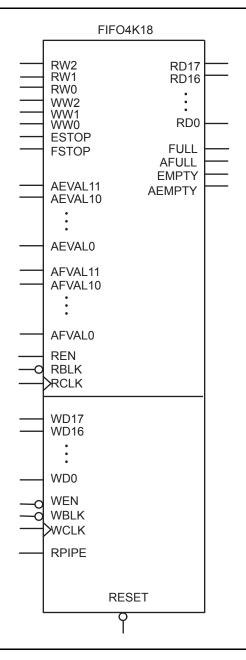


Figure 2-36 • FIFO Model



# **JTAG 1532 Characteristics**

JTAG timing delays do not include JTAG I/Os. To obtain complete JTAG timing, add I/O buffer delays to the corresponding standard selected; refer to the I/O timing characteristics in the "User I/O Characteristics" section on page 2-15 for more details.

# **Timing Characteristics**

### *Table 2-125* • JTAG 1532

```
Commercial-Case Conditions: T<sub>J</sub> = 70°C, Worst-Case VCC = 1.425 V
```

Parameter	Description	-2	-1	Std.	Units
t <sub>DISU</sub>	Test Data Input Setup Time	0.50	0.57	0.67	ns
t <sub>DIHD</sub>	Test Data Input Hold Time	1.00	1.13	1.33	ns
t <sub>TMSSU</sub>	Test Mode Select Setup Time	0.50	0.57	0.67	ns
t <sub>TMDHD</sub>	Test Mode Select Hold Time	1.00	1.13	1.33	ns
t <sub>TCK2Q</sub>	Clock to Q (data out)	6.00	6.80	8.00	ns
t <sub>RSTB2Q</sub>	Reset to Q (data out)	20.00	22.67	26.67	ns
F <sub>TCKMAX</sub>	TCK Maximum Frequency	25.00	22.00	19.00	MHz
t <sub>TRSTREM</sub>	ResetB Removal Time	0.00	0.00	0.00	ns
t <sub>TRSTREC</sub>	ResetB Recovery Time	0.20	0.23	0.27	ns
t <sub>TRSTMPW</sub>	ResetB Minimum Pulse	TBD	TBD	TBD	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.



# 3 – Pin Descriptions

# **Supply Pins**

#### Ground

Ground supply voltage to the core, I/O outputs, and I/O logic.

#### GNDQ Ground (quiet)

Quiet ground supply voltage to input buffers of I/O banks. Within the package, the GNDQ plane is decoupled from the simultaneous switching noise originated from the output buffer ground domain. This minimizes the noise transfer within the package and improves input signal integrity. GNDQ must always be connected to GND on the board.

#### VCC

GND

#### Core Supply Voltage

Supply voltage to the FPGA core, nominally 1.5 V. VCC is required for powering the JTAG state machine in addition to VJTAG. Even when a device is in bypass mode in a JTAG chain of interconnected devices, both VCC and VJTAG must remain powered to allow JTAG signals to pass through the device.

#### VCCIBx I/O Supply Voltage

Supply voltage to the bank's I/O output buffers and I/O logic. Bx is the I/O bank number. There are up to eight I/O banks on low power flash devices plus a dedicated VJTAG bank. Each bank can have a separate VCCI connection. All I/Os in a bank will run off the same VCCIBx supply. VCCI can be 1.5 V, 1.8 V, 2.5 V, or 3.3 V, nominal voltage. In general, unused I/O banks should have their corresponding VCCIX pins tied to GND. If an output pad is terminated to ground through any resistor and if the corresponding VCCIX is left floating, then the leakage current to ground is ~ 0uA. However, if an output pad is terminated to ground is ~ 3 uA. For unused banks the aforementioned behavior is to be taken into account while deciding if it's better to float VCCIX of unused bank or tie it to GND.

### VMVx I/O Supply Voltage (quiet)

Quiet supply voltage to the input buffers of each I/O bank. *x* is the bank number. Within the package, the VMV plane biases the input stage of the I/Os in the I/O banks. This minimizes the noise transfer within the package and improves input signal integrity. Each bank must have at least one VMV connection, and no VMV should be left unconnected. All I/Os in a bank run off the same VMVx supply. VMV is used to provide a quiet supply voltage to the input buffers of each I/O bank. VMVx can be 1.5 V, 1.8 V, 2.5 V, or 3.3 V, nominal voltage. Unused I/O banks should have their corresponding VMV pins tied to GND. VMV and VCCI should be at the same voltage within a given I/O bank. Used VMV pins must be connected to the corresponding VCCI pins of the same bank (i.e., VMV0 to VCCIB0, VMV1 to VCCIB1, etc.).

### VCCPLA/B/C/D/E/F PLL Supply Voltage

Supply voltage to analog PLL, nominally 1.5 V.

When the PLLs are not used, the Designer place-and-route tool automatically disables the unused PLLs to lower power consumption. The user should tie unused VCCPLx and VCOMPLx pins to ground. Microsemi recommends tying VCCPLx to VCC and using proper filtering circuits to decouple VCC noise from the PLLs. Refer to the PLL Power Supply Decoupling section of the "Clock Conditioning Circuits in IGLOO and ProASIC3 Devices" chapter of the *ProASIC3 FPGA Fabric User's Guide* for a complete board solution for the PLL analog power supply and ground.

There is one VCCPLF pin on ProASIC3 devices.

#### VCOMPLA/B/C/D/E/F PLL Ground

Ground to analog PLL power supplies. When the PLLs are not used, the Designer place-and-route tool automatically disables the unused PLLs to lower power consumption. The user should tie unused VCCPLx and VCOMPLx pins to ground.

There is one VCOMPLF pin on ProASIC3 devices.



## VJTAG

#### JTAG Supply Voltage

Low power flash devices have a separate bank for the dedicated JTAG pins. The JTAG pins can be run at any voltage from 1.5 V to 3.3 V (nominal). Isolating the JTAG power supply in a separate I/O bank gives greater flexibility in supply selection and simplifies power supply and PCB design.

If the JTAG interface is neither used nor planned for use, the VJTAG pin together with the TRST pin could be tied to GND.

It should be noted that VCC is required to be powered for JTAG operation; VJTAG alone is insufficient. If a device is in a JTAG chain of interconnected boards, the board containing the device can be powered down, provided both VJTAG and VCC to the part remain powered; otherwise, JTAG signals will not be able to transition the device, even in bypass mode.

Microsemi recommends that VPUMP and VJTAG power supplies be kept separate with independent filtering capacitors rather than supplying them from a common rail.

#### VPUMP Programming Supply Voltage

ProASIC3 devices support single-voltage ISP of the configuration flash and FlashROM. For programming, VPUMP should be 3.3 V nominal. During normal device operation, VPUMP can be left floating or can be tied (pulled up) to any voltage between 0 V and the VPUMP maximum. Programming power supply voltage (VPUMP) range is listed in Table 2-2 on page 2-2.

When the VPUMP pin is tied to ground, it will shut off the charge pump circuitry, resulting in no sources of oscillation from the charge pump circuitry.

For proper programming, 0.01  $\mu$ F and 0.33  $\mu$ F capacitors (both rated at 16 V) are to be connected in parallel across VPUMP and GND, and positioned as close to the FPGA pins as possible.

Microsemi recommends that VPUMP and VJTAG power supplies be kept separate with independent filtering capacitors rather than supplying them from a common rail.

# **User Pins**

I/O

#### User Input/Output

The I/O pin functions as an input, output, tristate, or bidirectional buffer. Input and output signal levels are compatible with the I/O standard selected.

During programming, I/Os become tristated and weakly pulled up to  $V_{CCI}$ . With  $V_{CCI}$ , VMV, and  $V_{CC}$  supplies continuously powered up, when the device transitions from programming to operating mode, the I/Os are instantly configured to the desired user configuration.

Unused I/Os are configured as follows:

- Output buffer is disabled (with tristate value of high impedance)
- Input buffer is disabled (with tristate value of high impedance)
- Weak pull-up is programmed

#### GL Globals

GL I/Os have access to certain clock conditioning circuitry (and the PLL) and/or have direct access to the global network (spines). Additionally, the global I/Os can be used as regular I/Os, since they have identical capabilities. Unused GL pins are configured as inputs with pull-up resistors.

See more detailed descriptions of global I/O connectivity in the "Clock Conditioning Circuits in IGLOO and ProASIC3 Devices" chapter of the *ProASIC3 FPGA Fabric User's Guide*. All inputs labeled GC/GF are direct inputs into the quadrant clocks. For example, if GAA0 is used for an input, GAA1 and GAA2 are no longer available for input to the quadrant globals. All inputs labeled GC/GF are direct inputs into the chip-level globals, and the rest are connected to the quadrant globals. The inputs to the global network are multiplexed, and only one input can be used as a global input.

Refer to the I/O Structure section of the handbook for the device you are using for an explanation of the naming of global pins.

#### FF Flash\*Freeze Mode Activation Pin

Flash\*Freeze is available on IGLOO, ProASIC3L, and RT ProASIC3 devices. It is not supported on ProASIC3/E devices. The FF pin is a dedicated input pin used to enter and exit Flash\*Freeze mode. The FF pin is active-low, has the same characteristics as a single-ended I/O, and must meet the maximum rise and fall times. When Flash\*Freeze



QN68		
Pin Number A3P030 Function		
1	IO82RSB1	
2	IO80RSB1	
3	IO78RSB1	
4	IO76RSB1	
5	GEC0/IO73RSB1	
6	GEA0/IO72RSB1	
7	GEB0/IO71RSB1	
8	VCC	
9	GND	
10	VCCIB1	
11	IO68RSB1	
12	IO67RSB1	
13	IO66RSB1	
14	IO65RSB1	
15	IO64RSB1	
16	IO63RSB1	
17	IO62RSB1	
18	IO60RSB1	
19	IO58RSB1	
20	IO56RSB1	
21	IO54RSB1	
22	IO52RSB1	
23	IO51RSB1	
24	VCC	
25	GND	
26	VCCIB1	
27	IO50RSB1	
28	IO48RSB1	
29	IO46RSB1	
30	IO44RSB1	
31	IO42RSB1	
32	ТСК	
33	TDI	
34	TMS	
35	VPUMP	
36	TDO	

QN68		
Pin Number	A3P030 Function	
37	TRST	
38	VJTAG	
39	IO40RSB0	
40	IO37RSB0	
41	GDB0/IO34RSE	
42	GDA0/IO33RSE	
43	GDC0/IO32RSE	
44	VCCIB0	
45	GND	
46	VCC	
47	IO31RSB0	
48	IO29RSB0	
49	IO28RSB0	
50	IO27RSB0	
51	IO25RSB0	
52	IO24RSB0	
53	IO22RSB0	
54	IO21RSB0	
55	IO19RSB0	
56	IO17RSB0	
57	IO15RSB0	
58	IO14RSB0	
59	VCCIB0	
60	GND	
61	VCC	
62	IO12RSB0	
63	IO10RSB0	
64	IO08RSB0	
65	IO06RSB0	
66	IO04RSB0	
67	IO02RSB0	
68	IO00RSB0	



Package Pin Assignments

QN132		
Pin Number	A3P250 Function	
C17	IO74RSB2	
C18	VCCIB2	
C19	ТСК	
C20	VMV2	
C21	VPUMP	
C22	VJTAG	
C23	VCCIB1	
C24	IO53NSB1	
C25	IO51NPB1	
C26	GCA1/IO50PPB1	
C27	GCC0/IO48NDB1	
C28	VCCIB1	
C29	IO42NDB1	
C30	GNDQ	
C31	GBA1/IO40RSB0	
C32	GBB0/IO37RSB0	
C33	VCC	
C34	IO24RSB0	
C35	IO19RSB0	
C36	IO16RSB0	
C37	IO10RSB0	
C38	VCCIB0	
C39	GAB1/IO03RSB0	
C40	VMV0	
D1	GND	
D2	GND	
D3	GND	
D4	GND	

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Package Pin Assignments

	PQ208		PQ208	PQ208	
Pin Number	A3P125 Function	Pin Number	A3P125 Function	Pin Number	A3P125 Function
109	TRST	145	IO46RSB0	181	IO21RSB0
110	VJTAG	146	NC	182	IO20RSB0
111	GDA0/IO66RSB0	147	NC	183	IO19RSB0
112	GDA1/IO65RSB0	148	NC	184	IO18RSB0
113	GDB0/IO64RSB0	149	GBC2/IO45RSB0	185	IO17RSB0
114	GDB1/IO63RSB0	150	IO44RSB0	186	VCCIB0
115	GDC0/IO62RSB0	151	GBB2/IO43RSB0	187	VCC
116	GDC1/IO61RSB0	152	IO42RSB0	188	IO16RSB0
117	NC	153	GBA2/IO41RSB0	189	IO15RSB0
118	NC	154	VMV0	190	IO14RSB0
119	NC	155	GNDQ	191	IO13RSB0
120	NC	156	GND	192	IO12RSB0
121	NC	157	NC	193	IO11RSB0
122	GND	158	GBA1/IO40RSB0	194	IO10RSB0
123	VCCIB0	159	GBA0/IO39RSB0	195	GND
124	NC	160	GBB1/IO38RSB0	196	IO09RSB0
125	NC	161	GBB0/IO37RSB0	197	IO08RSB0
126	VCC	162	GND	198	IO07RSB0
127	IO60RSB0	163	GBC1/IO36RSB0	199	IO06RSB0
128	GCC2/IO59RSB0	164	GBC0/IO35RSB0	200	VCCIB0
129	GCB2/IO58RSB0	165	IO34RSB0	201	GAC1/IO05RSB0
130	GND	166	IO33RSB0	202	GAC0/IO04RSB0
131	GCA2/IO57RSB0	167	IO32RSB0	203	GAB1/IO03RSB0
132	GCA0/IO56RSB0	168	IO31RSB0	204	GAB0/IO02RSB0
133	GCA1/IO55RSB0	169	IO30RSB0	205	GAA1/IO01RSB0
134	GCB0/IO54RSB0	170	VCCIB0	206	GAA0/IO00RSB0
135	GCB1/IO53RSB0	171	VCC	207	GNDQ
136	GCC0/IO52RSB0	172	IO29RSB0	208	VMV0
137	GCC1/IO51RSB0	173	IO28RSB0		
138	IO50RSB0	174	IO27RSB0		
139	IO49RSB0	175	IO26RSB0		
140	VCCIB0	176	IO25RSB0		
141	GND	177	IO24RSB0		
142	VCC	178	GND		
143	IO48RSB0	179	IO23RSB0		
144	IO47RSB0	180	IO22RSB0		



	FG484		FG484		FG484
Pin Number	A3P600 Function	Pin Number	A3P600 Function	Pin Number	A3P600 Function
A1	GND	B15	NC	D7	GAB0/IO02RSB0
A2	GND	B16	IO47RSB0	D8	IO11RSB0
A3	VCCIB0	B17	IO49RSB0	D9	IO16RSB0
A4	NC	B18	NC	D10	IO18RSB0
A5	NC	B19	NC	D11	IO28RSB0
A6	IO09RSB0	B20	NC	D12	IO34RSB0
A7	IO15RSB0	B21	VCCIB1	D13	IO37RSB0
A8	NC	B22	GND	D14	IO41RSB0
A9	NC	C1	VCCIB3	D15	IO43RSB0
A10	IO22RSB0	C2	NC	D16	GBB1/IO57RSB0
A11	IO23RSB0	C3	NC	D17	GBA0/IO58RSB0
A12	IO29RSB0	C4	NC	D18	GBA1/IO59RSB0
A13	IO35RSB0	C5	GND	D19	GND
A14	NC	C6	NC	D20	NC
A15	NC	C7	NC	D21	NC
A16	IO46RSB0	C8	VCC	D22	NC
A17	IO48RSB0	C9	VCC	E1	NC
A18	NC	C10	NC	E2	NC
A19	NC	C11	NC	E3	GND
A20	VCCIB0	C12	NC	E4	GAB2/IO173PDB3
A21	GND	C13	NC	E5	GAA2/IO174PDB3
A22	GND	C14	VCC	E6	GNDQ
B1	GND	C15	VCC	E7	GAB1/IO03RSB0
B2	VCCIB3	C16	NC	E8	IO13RSB0
B3	NC	C17	NC	E9	IO14RSB0
B4	NC	C18	GND	E10	IO21RSB0
B5	NC	C19	NC	E11	IO27RSB0
B6	IO08RSB0	C20	NC	E12	IO32RSB0
B7	IO12RSB0	C21	NC	E13	IO38RSB0
B8	NC	C22	VCCIB1	E14	IO42RSB0
B9	NC	D1	NC	E15	GBC1/IO55RSB0
B10	IO17RSB0	D2	NC	E16	GBB0/IO56RSB0
B11	NC	D3	NC	E17	IO52RSB0
B12	NC	D4	GND	E18	GBA2/IO60PDB1
B13	IO36RSB0	D5	GAA0/IO00RSB0	E19	IO60NDB1
B14	NC	D6	GAA1/IO01RSB0	E20	GND

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Package Pin Assignments

FG484		
Pin Number	A3P1000 Function	
Y15	VCC	
Y16	NC	
Y17	NC	
Y18	GND	
Y19	NC	
Y20	NC	
Y21	NC	
Y22	VCCIB1	
AA1	GND	
AA2	VCCIB3	
AA3	NC	
AA4	IO181RSB2	
AA5	IO178RSB2	
AA6	IO175RSB2	
AA7	IO169RSB2	
AA8	IO166RSB2	
AA9	IO160RSB2	
AA10	IO152RSB2	
AA11	IO146RSB2	
AA12	IO139RSB2	
AA13	IO133RSB2	
AA14	NC	
AA15	NC	
AA16	IO122RSB2	
AA17	IO119RSB2	
AA18	IO117RSB2	
AA19	NC	
AA20	NC	
AA21	VCCIB1	
AA22	GND	
AB1	GND	
AB2	GND	
AB3	VCCIB2	
AB4	IO180RSB2	
AB5	IO176RSB2	
AB6	IO173RSB2	

FG484		
Pin Number	A3P1000 Function	
AB7	IO167RSB2	
AB8	IO162RSB2	
AB9	IO156RSB2	
AB10	IO150RSB2	
AB11	IO145RSB2	
AB12	IO144RSB2	
AB13	IO132RSB2	
AB14	IO127RSB2	
AB15	IO126RSB2	
AB16	IO123RSB2	
AB17	IO121RSB2	
AB18	IO118RSB2	
AB19	NC	
AB20	VCCIB2	
AB21	GND	
AB22	GND	

Revision	Changes	Page
Revision 2 (cont'd)	The "ProASIC3 FPGAs Package Sizes Dimensions" table is new.	Ш
	In the "ProASIC3 Ordering Information", the QN package measurements were updated to include both 0.4 mm and 0.5 mm.	IV
	In the General Description section the number of I/Os was updated from 288 to 300.	1-1
Packaging v1.2	The "QN68 – Bottom View" section is new.	4-3
<b>Revision 1 (Feb 2008)</b> DC and Switching Characteristics v1.1	In Table 2-2 • Recommended Operating Conditions 1, $T_J$ was listed in the symbol column and was incorrect. It was corrected and changed to $T_A$ .	2-2
	In Table 2-3 • Flash Programming Limits – Retention, Storage and Operating Temperature, Maximum Operating Junction Temperature was changed from 110°C to 100°C for both commercial and industrial grades.	2-3
	The "PLL Behavior at Brownout Condition" section is new.	2-4
	In the "PLL Contribution—PPLL" section, the following was deleted: FCLKIN is the input clock frequency.	2-14
	In Table 2-21 • Summary of Maximum and Minimum DC Input Levels, the note was incorrect. It previously said $T_J$ and it was corrected and changed to $T_A$ .	2-21
	In Table 2-115 • ProASIC3 CCC/PLL Specification, the SCLK parameter and note 1 are new.	2-90
	Table 2-125 • JTAG 1532 was populated with the parameter data, which was not in the previous version of the document.	2-108
Packaging v1.1	In the "VQ100" A3P030 pin table, the function of pin 63 was incorrect and changed from IO39RSB0 to GDB0/IO38RSB0.	4-19
Revision 0 (Jan 2008)	This document was previously in datasheet v2.2. As a result of moving to the handbook format, Actel has restarted the version numbers.	N/A
v2.2 (July 2007)	The M7 and M1 device part numbers have been updated in Table 1 • ProASIC3 Product Family, "I/Os Per Package", "Automotive ProASIC3 Ordering Information", "Temperature Grade Offerings", and "Speed Grade and Temperature Grade Matrix".	i, ii, iii, iii, iv
	The words "ambient temperature" were added to the temperature range in the "Automotive ProASIC3 Ordering Information", "Temperature Grade Offerings", and "Speed Grade and Temperature Grade Matrix" sections.	iii, iv
	The T <sub>J</sub> parameter in Table 3-2 $\cdot$ Recommended Operating Conditions was changed to T <sub>A</sub> , ambient temperature, and table notes 4–6 were added.	3-2
v2.1 (May 2007)	In the "Clock Conditioning Circuit (CCC) and PLL" section, the Wide Input Frequency Range (1.5 MHz to 200 MHz) was changed to (1.5 MHz to 350 MHz).	i
	The "Clock Conditioning Circuit (CCC) and PLL" section was updated.	i
	In the "I/Os Per Package" section, the A3P030, A3P060, A3P125, ACP250, and A3P600 device I/Os were updated.	ii
	Table 3-5 • Package Thermal Resistivities was updated with A3P1000information. The note below the table is also new.	3-5



Datasheet Information

Revision	Changes	Page
Advance v0.3	The "PLL Macro" section was updated. EXTFB information was removed from this section.	2-15
	The CCC Output Peak-to-Peak Period Jitter F <sub>CCC_OUT</sub> was updated in Table 2- 11 • ProASIC3 CCC/PLL Specification	2-29
	EXTFB was removed from Figure 2-27 • CCC/PLL Macro.	2-28
	Table 2-13 • ProASIC3 I/O Features was updated.	2-30
	The "Hot-Swap Support" section was updated.	2-33
	The "Cold-Sparing Support" section was updated.	2-34
	"Electrostatic Discharge (ESD) Protection" section was updated.	2-35
	The LVPECL specification in Table 2-43 • I/O Hot-Swap and 5 V Input Tolerance Capabilities in ProASIC3 Devices was updated.	2-64
	In the Bank 1 area of Figure 2-72, VMV2 was changed to VMV1 and VCCIB2 was changed to VCC_IB1.	2-97
	The VJTAG and I/O pin descriptions were updated in the "Pin Descriptions" section.	2-50
	The "JTAG Pins" section was updated.	2-51
	"128-Bit AES Decryption" section was updated to include M7 device information.	2-53
	Table 3-6 was updated.	3-6
	Table 3-7 was updated.	3-6
	In Table 3-11, PAC4 was updated.	3-93-8
	Table 3-20 was updated.	3-20
	The note in Table 3-32 was updated.	3-27
	All Timing Characteristics tables were updated from LVTTL to Register Delays	3-31 to 3- 73
	The Timing Characteristics for RAM4K9, RAM512X18, and FIFO were updated.	3-85 to 3-90
	F <sub>TCKMAX</sub> was updated in Table 3-110.	3-97
Advance v0.2	Figure 2-11 was updated.	2-9
	The "Clock Resources (VersaNets)" section was updated.	2-9
	The "VersaNet Global Networks and Spine Access" section was updated.	2-9
	The "PLL Macro" section was updated.	2-15
	Figure 2-27 was updated.	2-28
	Figure 2-20 was updated.	2-19
	Table 2-5 was updated.	2-25
	Table 2-6 was updated.	2-25
	The "FIFO Flag Usage Considerations" section was updated.	2-27
	Table 2-13 was updated.	2-30
	Figure 2-24 was updated.	2-31
	The "Cold-Sparing Support" section is new.	2-34